

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI AVD035P** is a medium power Class C transistor for pulsed L-Band avionics, DME/TACAN Applications.

**FEATURES:**

- Internal Input Matching Network
- $P_G = 10$  dB at 35 W/1150 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	3.0 A PEAK
$V_{CB}$	55 V
$P_{DISS}$	100 W PEAK
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	1.0 °C/W

**PACKAGE STYLE .280 4L PILL (A)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.195 / 4.95	.205 / 5.21
C	1.000 / 25.40	
D	.004 / 0.10	.007 / 0.18
E	.050 / 1.27	.065 / 1.65
F		.145 / 3.68
G	.275 / 6.99	.285 / 7.21

**ORDER CODE: ASI10559**

**CHARACTERISTICS**  $T_C = 25$  °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 10$ mA	65			V
$BV_{CER}$	$I_C = 10$ mA $R_{BE} = 10$ $\Omega$	65			V
$BV_{EBO}$	$I_E = 1$ mA	3.5			V
$I_{CES}$	$V_{CE} = 50$ V			5.0	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 500$ mA	15		120	---
$P_G$	$V_{CC} = 50$ V $P_{OUT} = 35$ W $f = 1025 - 1150$ MHz	10.7	11.2		dB
$\eta_c$	$P_{IN} = 3.0$ W	43	48		%